

FGW35N60HD

Discrete IGBT

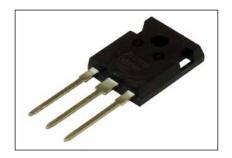
Discrete IGBT (High-Speed V series) 600V / 35A

■ Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

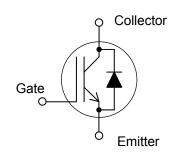
Uninterruptible power supply Power coditionner Power factor correction circuit



Equivalent circuit

■ Maximum Ratings and Characteristics ■ Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	Vces	600	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
DC Collector Current	I _{C@25}	64	Α	Tc=25°C,Tj=150°C
	Ic@100	35	Α	Tc=100°C,Tj=150°C
Pulsed Collector Current	ICP	105	Α	Note *1
Turn-Off Safe Operating Area	-	105	Α	Vce≤600V,Tj≤175°C
Diode Forward Current	I _{F@25}	30	Α	
	IF@100	15	Α	
Diode Pulsed Current	I _{FP}	105	Α	Note *1
Short Circuit Withstand Time	tsc	5	μs	Vcc≤300V,VGE=12V Tj≤150°C
IGBT Max. Power Dissipation	P _{D_IGBT}	230	W	Tc=25°C
FWD Max. Power Dissipation	P _{D_FWD}	80	٧V	Tc=25°C
Operating Junction Temperature	T _j	-40 ~ +175	ů	
Storage Temperature	T _{stg}	-55 ~ +175	°C	



Note *1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T_i= 25°C unless otherwise specified)

Items	Symbols	Symbols Conditions			Characteristics		
items	Symbols	Conditions		min.	typ.	max.	Units
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	Ic = 250µA, V _{GE} = 0V		600	-	-	V
Zero Gate Voltage Collector Current	Ices	V _{CE} = 600V, V _{GE} = 0V	T _i =25°C	-	-	250	μA
	ICES		T _i =175°C	-	-	10	mA
Gate-Emitter Leakage Current	Iges	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	200	nA
Gate-Emitter Threshold Voltage	V _{GE (th)}	$V_{CE} = +20V, I_{C} = 35mA$		4.0	5.0	6.0	V
Collector-Emitter Saturation Voltage	V _{CE} (sat)	V _{GE} = +15V, I _C = 35A	T _i =25°C	-	1.50	1.95	V
Collector-Emitter Saturation Voltage			T _j =175°C	-	1.80	-	V
Input Capacitance	Cies	V _{CE} =25V	V _{CE} =25V V _{GE} =0V		2800	-	pF
Output Capacitance	Coes	V _{GE} =0V			140	-	
Reverse Transfer Capacitance	Cres	f=1MHz		-	100	-	
		Vcc = 400V					
Gate Charge	Q _G	Ic = 35A	-	210	-	nC	
		V _{GE} = 15V					
Turn-On Delay Time	t _{d(on)}	$T_j = 25^{\circ}C$	-	32	-	ns	
Rise Time	t	Vcc = 400V	-	60	-		
Turn-Off Delay Time	t _{d(off)}	Ic = 35A	-	200	-		
Fall Time	tr	V _{GE} = 15V	-	40	-		
Turn-On Energy	Eon	$R_G = 10\Omega$	-	0.90	-		
		L = 500µH Energy loss include "tail" and FWD reverse					mJ
Turn-Off Energy	Eoff			-	0.85	-	""
		recovery.					
Turn-On Delay Time	t _{d(on)}	$T_i = 175^{\circ}C$ - 33			-		
Rise Time	t		Vcc = 400V		60	-	ns
Turn-Off Delay Time	t _{d(off)}	Ic = 35A		-	225	-	
Fall Time	t _f	V _{GE} = 15V		-	50	-	
Turn-On Energy	Eon	$R_G = 10\Omega$		-	1.40	-	
		L = 500µH					mJ
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse		-	1.25	-	1110
		recovery.					

http://www.fujielectric.com/products/semiconductor/

● FWD Characteristics

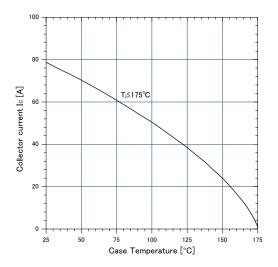
Description	Cumbal	Conditions	Canditions		Characteristics		
Description	Symbol	Conditions		min.	typ.	max.	Unit
Forward Voltage Drop	VF	I=15A	T _i =25°C	-	2.0	2.6	V
	VF	IF- IDA	T _j =175°C	-	1.4	-	V
Diode Reverse Recovery Time	+	Vcc=30V,I _F = 1.5A			24	31	ns
	Trr1	-di/dt=200A/µs		-			
Diode Reverse Recovery Time	t _{rr2}	Vcc=400V			0.03	_	μs
Diode Reverse Recovery Time	UTZ	I _F =15A		0.00		μο	
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/µs		_	0.06	_	μC
Blodd Noveled Neddvery Charge	Q.II	T _j =25°C			0.00		μο
Diode Reverse Recovery Time	t _{rr2}	Vcc=400V		_	0.15	_	μs
	U-12	IF=15A			5.10		F-0
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/µs		_	0.65	_	μC
	J 3.11	T _i =175°C			0.00	_	ا ۳۵

● Thermal resistance characteristics

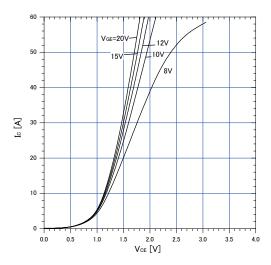
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	Units
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	-	50	
Thermal Resistance, IGBT Junction to Case	R _{th(j-c)_IGBT}	-	-	-	0.641	°C/W
Thermal Resistance, FWD Junction to Case	R _{th(j-c)_FWD}	-	-	-	1.786	

■ Characteristics (Representative)

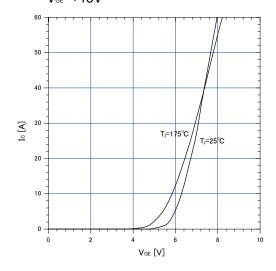
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 175$ °C



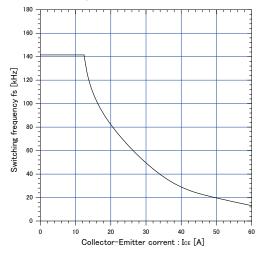
Graph.3
Typical Output Characteristics (V_{c∈}-I_c)
T,=25°C



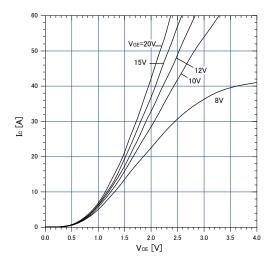
Graph.5 Typical Transfer Characteristics V_{GE} =+15V



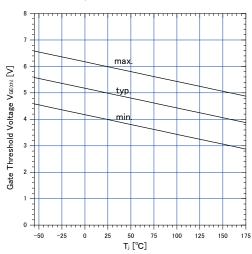
Graph.2 Collector Current vs. switching frequency V_{ce} =+15V, T_{c} ≤175°C, V_{cc} =400V, D=0.5, R_{e} =10 Ω , T_{c} =100°C



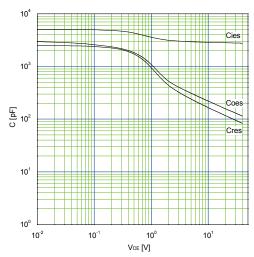
Graph.4
Typical Output Characteristics (V_{c∈}-I_c)
T_i=175°C



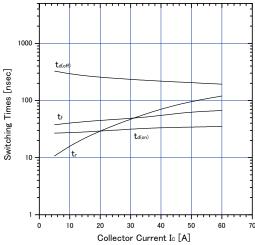
Graph.6
Gate Threshold Voltage vs. T_i
I_o=35mA, V_{oe}=20V



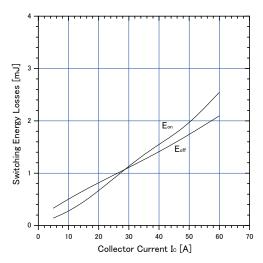
Graph.7 Typical Capacitance V₀=0V,f=1MHz,T,=25°C



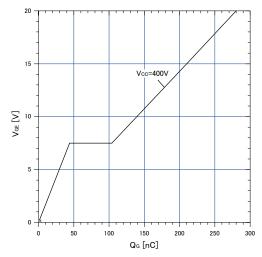
Graph.9 Typical switching time vs. I_c T_i=175°C,V_{cc}=400V,L=500 μ H V_{cE}=15V,R_c=10 Ω



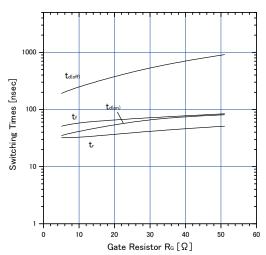
Graph.11 Typical switching losses vs. Io $T_{\rm J}=175^{\circ}{\rm C}, V_{\rm cc}=400{\rm V}, L=500\mu{\rm H}$ $V_{\rm cc}=15{\rm V}, R_{\rm c}=10\Omega$



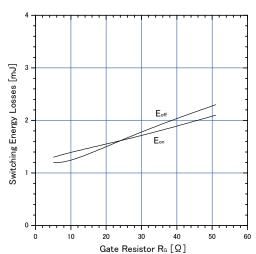
Graph.8 Typical Gate Charge Vcc=400V,Ic=35A,T;=25°C



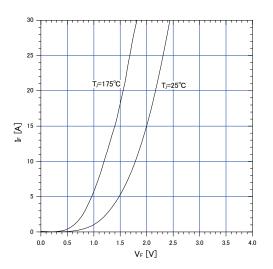
Graph.10
Typical switching time vs. R_s
T_i=175°C,V_{cc}=400V,I_c=35A,L=500μH
V_{se}=15V



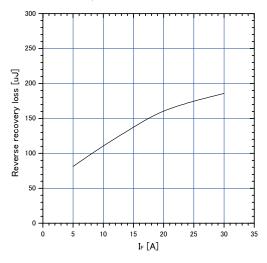
Graph.12 Typical switching losses vs. R_s T_j =175°C, V_{cc} =400V, I_c =35A,L=500 μ H V_{ce} =15V



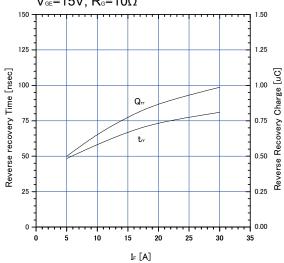
Graph.13 FWD Forward voltage drop (V_F-I_F)



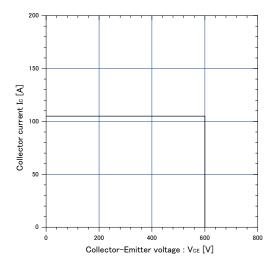
Graph.15 Typical reverse recovery loss vs. I_F $T_{\rm J}=175^{\circ}C$, $V_{\rm cc}=400V$, $L=500\mu H$ $V_{\rm cE}=15V$, $R_{\rm c}=10\Omega$



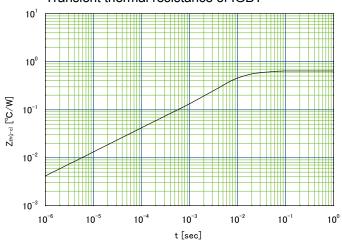
Graph.14 Typical reverse recovery characteristics vs. I_{F} T_{J} =175°C, V_{cc} =400V, L=500 μH V_{ce} =15V, R_{c} =10 Ω



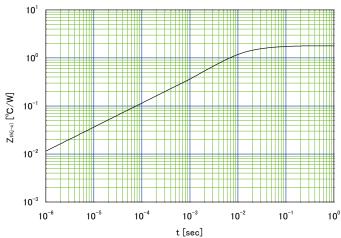
Graph.16 Reverse biased Safe Operating Area $T_1 \le 175^{\circ}C$, $V_{\text{GE}} = +15 \text{V/OV}$, $R_{\text{G}} = 10 \Omega$



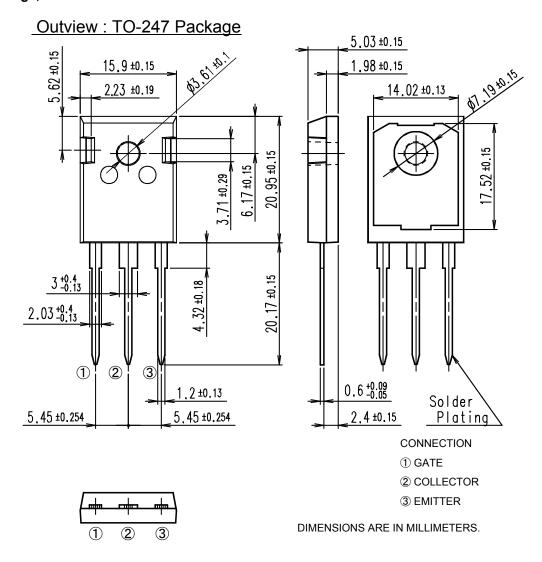
Graph.17 Transient thermal resistance of IGBT



Graph.18
Transient thermal resistance of FWD



■ Outline Drawings, mm



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